

1SS187

PRV : 85 Volts
Io : 100 mA

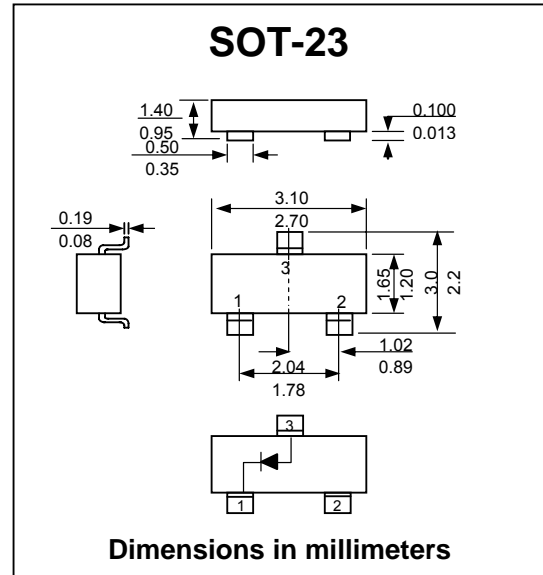
FEATURES :

- * Small package
- * Low forward voltage
- * Fast reverse recovery time
- * Small total capacitance
- * **Pb / RoHS Free**

MECHANICAL DATA :

- * Case : SOT-23 plastic Case
- * Marking Code : D3

SILICON EPITAXIAL PLANAR DIODE



MAXIMUM RATINGS AND THERMAL CHARACTERISTICS (Ta =25 °C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V _{RM}	85	V
Reverse Voltage	V _R	80	V
Maximum Peak Forward Current	I _{FM}	300	mA
Average Forward Current	I _{F(AV)}	100	mA
Surge Current (10 ms)	I _{FSM}	2	A
Power Dissipation	P _{tot}	150	mW
Junction Temperature	T _J	125	°C
Storage Temperature Range	T _{STG}	-55 to +125	°C

ELECTRICAL CHARACTERISTICS (Ta =25 °C)

Parameter	Test Condition	Symbol	Min.	TYP	Max.	Unit
Forward Voltage	I _F = 100 mA	V _F	-	-	1.2	V
Reverse Current	V _R = 30 V	I _R	-	-	0.1	µA
	V _R = 80 V		-	-	0.5	
Total Capacitance	V _R = 0 V, f = 1 MHz	C _T	-	-	4	pF
Reverse Recovery Time	I _F = 10 mA	T _{rr}	-	-	4	ns

RATINGS AND CHARACTERISTIC CURVES(1SS187)

FIG.1 - FORWARD CURRENT VS. FORWARD VOLTAGE

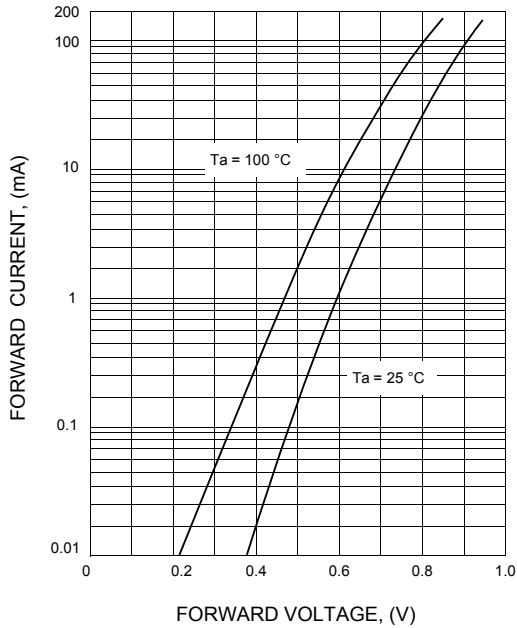


FIG.2 - REVERSE CURRENT VS. REVERSE VOLTAGE

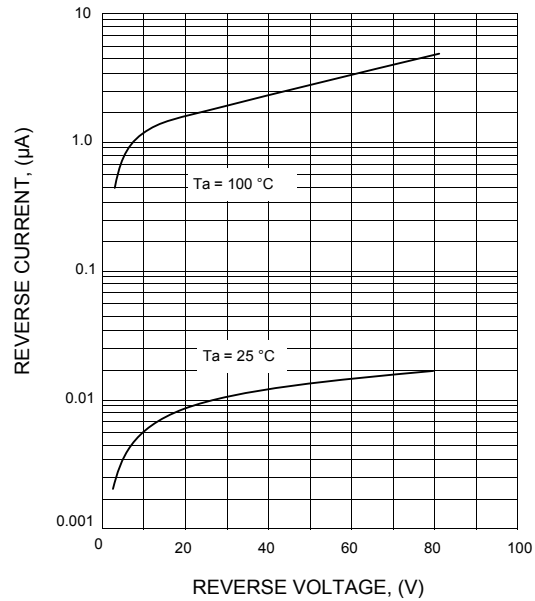


FIG.3 - TOTAL CAPACITANCE VS. REVERSE VOLTAGE

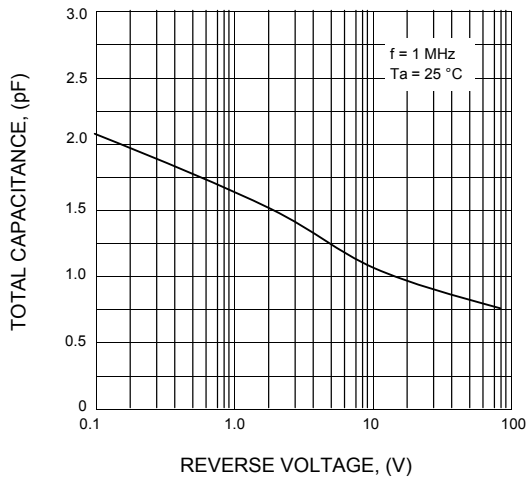


FIG.4 - REVERSE RECOVERY TIME VS. FORWARD CURRENT

